

**AMENDMENTS TO THE ABSTRACT**

Please make the following changes to the abstract now appearing in the currently filed specification:

~~There is provided an erroneous operation preventing circuit for preventing erroneous operation of reading out erroneous data in a circuit due to system noises, etc. when data in a memory array should be read out. [[The]]~~An erroneous operation preventing circuit of an electrically rewritable non-volatile memory device is for setting one or more operational modes of a plurality of operational modes including at least a first reading mode of reading out data from a memory array 4, a programming mode, an erasing mode and a second reading mode of reading out data not stored in the memory array 4, in accordance with an input control command, and for performing a predetermined process in the set operational modes. The erroneous operation preventing circuit[[,]] comprises an operational mode enforcing circuit 2a for setting the first reading mode regardless of the input of the control command, in a data protection status where the programming mode and the erasing mode are inhibited from being set in accordance with a control signal for protecting predetermined data.